



### P-CHANNEL ENHANCEMENT MODE MOSFET

## Product Summary (Typ. @ VGS = -4.5V, TA = +25°C)

BVDSS	RDS(ON)	Qg	Q <sub>gd</sub>	lο
-20V	40mΩ	2.3nC	0.4nC	-4.1A

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Battery Management
- Load Switch
- Battery Protection

## **Features**

- LD-MOS Technology with the Lowest Figure of Merit:  $R_{DS(ON)} = 40 m\Omega \text{ to Minimize On-State Losses} \\ Q_g = 2.3 nC \text{ for Ultra-Fast Switching}$
- V<sub>GS(th)</sub> = -0.8V typ. for a Low Turn-On Potential
- CSP with Footprint 1.0mm x 1.0mm
- Height = 0.62mm for Low Profile
- ESD = 3kV HBM Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
   A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

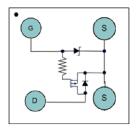
 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

## **Mechanical Data**

- Case: U-WLB1010-4
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal: Finish SnAgCu. Solderable per MIL-STD-202 Method 208 (e1)
- Weight: 0.0018 grams (Approximate)

#### U-WLB1010-4





Top View Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2047UCB4-7	U-WLB1010-4	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**

### U-WLB1010-4



DW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

c = Assembly Code

Date Code Key

Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Z		Н	ı	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

# 

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	-6	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-4.1 -3.2	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = -2.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-3.6 -2.8	А
Pulsed Drain Current (Note 6)			IDМ	-16	А

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	PD	1.0	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	127	°C/W
Thermal Resistance, Junction to Case @ T <sub>C</sub> = +25°C (Note 7)	Rejc	25.8	°C/W
Power Dissipation (Note 5)	PD	1.66	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	77	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
- Repetitive rating, pulse width limited by junction temperature.
   Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.

DMP2047UCB4 Document number: DS36154 Rev. 7 - 2



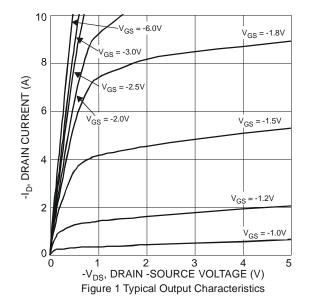
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

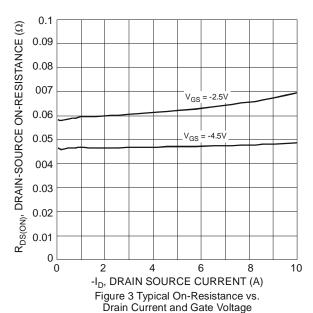
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	•	•	•	•		•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Gate-Source Breakdown Voltage	BVgss	-6.0	_	_	V	$V_{DS} = 0V, I_{G} = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	-1	μA	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	-100	nA	$V_{GS} = -6V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	Vgs(TH)	-0.4	-0.8	-1.2	<b>V</b>	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
Static Drain-Source On-Resistance	Process	_	40	47	mΩ	Vgs = -4.5V, ID =-1A
Static Dialif-Source Off-Resistance	Rds(on)	_	53	60	11122	$V_{GS} = -2.5V, I_D = -1A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	3.7	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1A
Diode Forward Voltage	VsD	_	-0.7	-1.0	V	Vgs = 0V, Is = -1A
Reverse Recovery Charge	Qrr	_	3.07	_	nC	V <sub>DD</sub> = -10V, I <sub>F</sub> = -1A,
Reverse Recovery Time	trr	_	13.14	_	ns	di/dt =100A/µs
DYNAMIC CHARACTERISTICS (Note 9)						•
Input Capacitance	Ciss	_	218	_		101/11/101/1
Output Capacitance	Coss	_	116	_	pF	$V_{DS} = -10V$ , $V_{GS} = 0V$ , $f = 1.0MHz$
Reverse Transfer Capacitance	Crss	_	11	_		1 – 1.01/11/2
Total Gate Charge	Qg	_	2.3	_		
Gate-Source Charge	Qgs	_	0.2	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ ,
Gate-Drain Charge	Q <sub>gd</sub>	_	0.4	_	IIC	$I_D = -1A$
Gate Charge at Vth	Q <sub>g(th)</sub>	_	0.2	_		
Turn-On Delay Time	t <sub>D</sub> (ON)	_	7.9	_		
Turn-On Rise Time	t <sub>R</sub>	_	10.7	_	20	$V_{DS} = -10V$ , $V_{GS} = -2.5V$ ,
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	48	_	ns	$R_G = 20\Omega$ , $I_D = -1A$
Turn-Off Fall Time	tF	_	38	_		

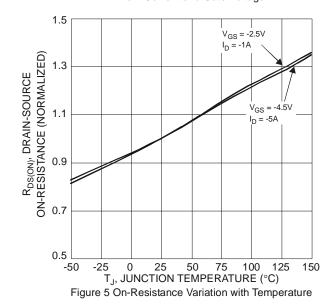
Notes:

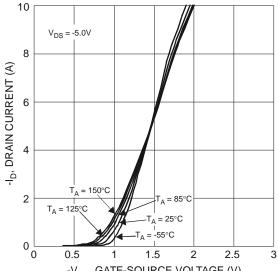
<sup>8.</sup> Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to production testing.



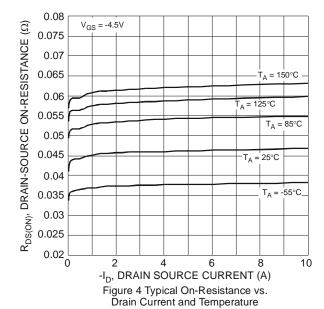








-V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2 Typical Transfer Characteristics



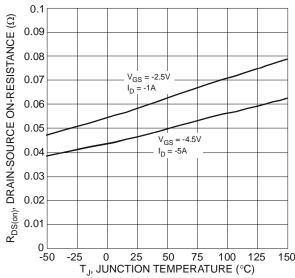


Figure 6 On-Resistance Variation with Temperature



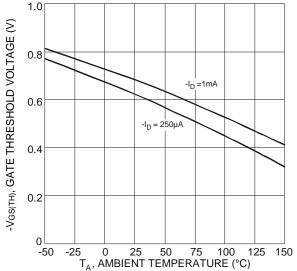


Figure 7 Gate Threshold Variation vs. Ambient Temperature

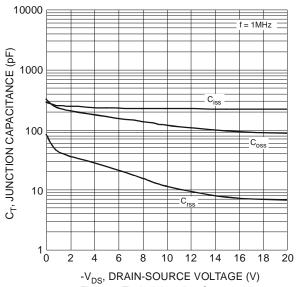
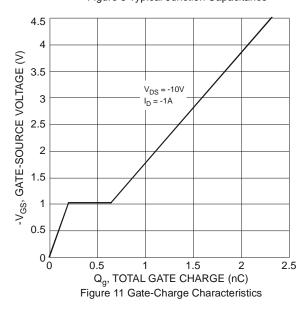
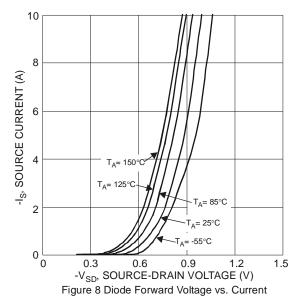


Figure 9 Typical Junction Capacitance





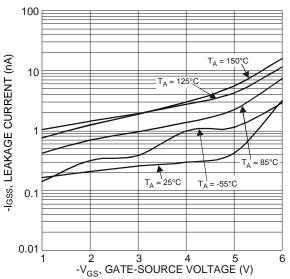
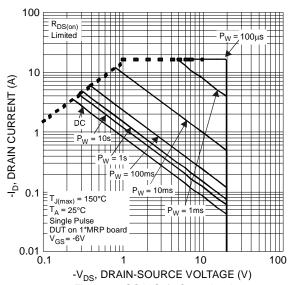
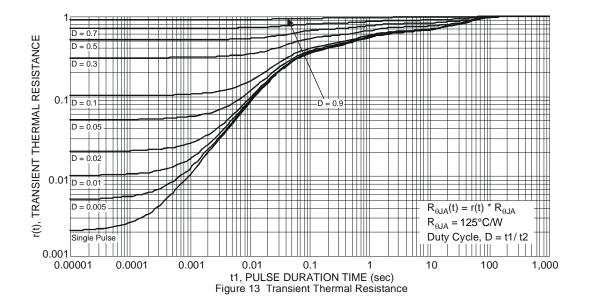


Figure 10 Typical Gate-Source Leakage Current vs. Voltage





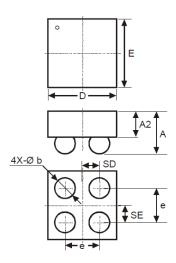




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-WLB1010-4

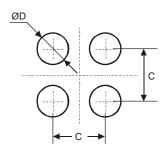


U-WLB1010-4					
Dim	Min	Max	Тур		
D	0.95	1.05	1.00		
E	0.95	1.05	1.00		
Α	-	0.62	_		
A2	_	_	0.38		
b	0.25	0.35	0.30		
е	_	_	0.50		
SD	_	_	0.25		
SE	_	_	0.25		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-WLB1010-4



Dimensions	Value (in mm)
С	0.50
D	0.25



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